

### Amendments to the Claims

This listing of claims will replace all prior versions, and listing, of claims in the application.

1. (Currently Amended) A thin film transistor comprising:
  - a gate electrode;
  - a gate insulating layer formed on the gate electrode;
  - a semiconductor layer formed on the gate insulating layer and disposed opposite the gate electrode;
  - a source electrode and a drain electrode that are formed at least in part on the semiconductor layer and face each other, the source electrode and the drain electrode each having branches, the branches of the source electrode extending toward the drain electrode, the branches of the drain electrode extending toward the source electrode, and the branches of the source electrode arranged in alternating manner with the branches of the drain electrode;
  - a passivation layer formed on the source electrode, the drain electrode, and a portion of the semiconductor layer that is not covered with the source electrode and the drain electrode; and
  - a shielding electrode formed on the passivation layer and disposed on a region between the source electrode and the drain electrode,
    - wherein the shielding electrode overlaps the gate electrode,
    - wherein the shielding electrode provides a common voltage shielding for the region on which it is disposed,
    - wherein the shielding electrode comprises a transparent electrode, and
    - wherein edges of the shielding electrode substantially overlap edges of the region between the source electrode and the drain electrode in plan view.
2. (Original) The thin film transistor of claim 1, wherein the shielding electrode is electrically isolated.

3. (Original) The thin film transistor of claim 1, wherein the shielding electrode is supplied with a predetermined voltage.

4. (Original) The thin film transistor of claim 3, wherein the predetermined voltage supplied to the shielding electrode is equal to or lower than a ground voltage.

5. (Original) The thin film transistor of claim 3, wherein the predetermined voltage supplied to the shielding electrode is a negative voltage.

6. (Original) The thin film transistor of claim 1, wherein the shielding electrode comprises IZO or ITO.

7. (Original) The thin film transistor of claim 1, wherein the shielding electrode has a shape of horseshoes.

8. (Original) The thin film transistor of claim 1, wherein the passivation layer comprises organic insulator.

9. (Currently Amended) A thin film transistor array panel comprising:  
a gate line and a data line;  
a first thin film transistor including a control electrode, an input electrode, an output electrode, and a channel portion disposed between the input electrode and the output electrode and generating a gate signal to be applied to the gate line;  
a second thin film transistor including a gate electrode connected to the gate line, a source electrode connected to the data line, a drain electrode, and a channel portion disposed between the source electrode and the drain electrode and transmitting a data signal from the data line in response to the gate signal from the gate line;  
a pixel electrode connected to the drain electrode to receive the data signal;  
a common electrode facing the pixel electrode; and  
a first shielding electrode disposed on the channel portion of the first thin film transistor,

wherein the first shielding electrode is formed of the same layer as the pixel electrode,

wherein the first shielding electrode overlaps the control electrode,

wherein when a common voltage is applied to a common electrode, a voltage lower than the common voltage is applied to the first shielding electrode, so that the shielding electrode provides a common voltage shielding for the area on which it is disposed, and

wherein edges of the shielding electrode substantially overlap edges of a region between the source electrode and the drain electrode in plan view.

10. (Original) The thin film transistor array panel of claim 9, wherein the first shielding electrode is electrically isolated.

11. (Original) The thin film transistor array panel of claim 9, wherein the first shielding electrode is supplied with a predetermined voltage.

12. (Original) The thin film transistor array panel of claim 11, wherein the predetermined voltage supplied to the first shielding electrode is equal to or lower than a ground voltage.

13. (Original) The thin film transistor array panel of claim 11, wherein the predetermined voltage supplied to the first shielding electrode is a negative voltage.

14. (Original) The thin film transistor array panel of claim 11, wherein the predetermined voltage supplied to the first shielding electrode has a magnitude for turning off the second thin film transistor.

15. (Cancelled)

16. (Original) The thin film transistor array panel of claim 9, further comprising a second shielding electrode disposed on the channel portions of the second thin film transistor and including the same layer as the pixel electrode.

17. (Original) The thin film transistor array panel of claim 16, further comprising an insulating layer disposed between the first and the second thin film transistors and the first and the second shielding electrodes.

18. (Original) The thin film transistor array panel of claim 17, wherein the insulating layer comprises organic material.

19. (Currently Amended) A display device comprising:

a gate line and a data line;

a first thin film transistor including a gate electrode, a source electrode, a drain electrode, and a channel portion disposed between the source electrode and the drain electrode and generating a gate signal to be applied to the gate line;

a second thin film transistor transmitting a data signal from the data line in response to the gate signal from the gate line;

a pixel electrode connected to the second thin film transistor to receive the data signal;

a shielding electrode disposed on the channel portion between the source electrode and the drain electrode of the first thin film transistor, wherein the shielding electrode is formed of the same layer as the pixel electrode, and wherein the shielding electrode overlaps the gate electrode; and

a common electrode facing the pixel electrode,

wherein when a common voltage is applied to the common electrode, a voltage lower than the common voltage is applied to the shielding electrode, so that the shielding electrode provides a common voltage shielding for the area on which it is disposed, and

wherein edges of the shielding electrode substantially overlap edges of a region between the source electrode and the drain electrode in plan view.

20. (Original) The display device of claim 19, wherein the shielding electrode faces the common electrode.

21. (Original) The display device of claim 20, wherein the shielding electrode is supplied with a predetermined voltage lower than a voltage applied to the common electrode.

22. (Original) The display device of claim 21, wherein the predetermined voltage supplied to the shielding electrode has a magnitude for turning off the second thin film transistor.

23. (Cancelled)

24. (Previously presented) The display device of claim 19 further comprising a dielectric layer disposed between the shielding electrode and the common electrode.

25. (Original) The display device of claim 24, wherein the dielectric layer comprises a liquid crystal layer.

26. (Previously presented) The thin film transistor of claim 1, wherein the shielding electrode is formed on a channel portion of the thin film transistor.

27. (Currently Amended) A thin film transistor array panel comprising:  
a gate line and a data line;  
a first thin film transistor including a control electrode, an input electrode, an output electrode, and a channel portion disposed between the input electrode and the output electrode and generating a gate signal to be applied to the gate line;  
a second thin film transistor including a gate electrode connected to the gate line, a source electrode connected to the data line, a drain electrode, and a channel portion disposed between the source electrode and the drain electrode and transmitting a data signal from the

data line in response to the gate signal from the gate line;  
a pixel electrode connected to the drain electrode to receive the data signal;  
a common electrode facing the pixel electrode; and  
a first shielding electrode disposed on the channel portion between the source electrode and the drain electrode of the second thin film transistor, wherein the second thin film transistor is formed of the same layer as the pixel electrode, and wherein the shielding electrode overlaps the gate electrode,  
wherein when a common voltage is applied to the common electrode, a voltage lower than the common voltage is applied to the first shielding electrode, so that the first shielding electrode provides a common voltage shielding for the area on which it is disposed, and  
~~wherein edges of the shielding electrode substantially overlap edges of a region between the source electrode and the drain electrode in plan view.~~

28. (Previously presented) The thin film transistor array panel of claim 27, further comprising a second shielding electrode disposed on the channel portion between the source electrode and the drain electrode of the first thin film transistor, wherein the second shielding electrode of the first thin film transistor is formed of the same layer as the pixel electrode.

29. (Previously presented) The thin film transistor array panel of claim 27, wherein the first shielding electrode is electrically isolated.

30. (Previously presented) The thin film transistor array panel of claim 27, wherein the first shielding electrode comprises a transparent electrode.

31. (Previously presented) The thin film transistor array panel of claim 27, wherein the first shielding electrode is supplied with a predetermined voltage.

32. (New) The thin film transistor array panel of claim 27, wherein the second thin film transistor is formed of the same layer as the pixel electrode.

33. (New) The thin film transistor array panel of claim 27, wherein the shielding electrode overlaps the gate electrode.

34. (New) The thin film transistor array panel of claim 27, wherein edges of the shielding electrode substantially overlap edges of a region between the source electrode and the drain electrode in plan view.